

SANYO	No.1637B	2SC3638
NPN Triple Diffused Planar Silicon Transistor VERY HIGH-DEFINITION DISPLAY HORIZONTAL DEFLECTION OUTPUT APPLICATIONS		

Features

- . High reliability (Adoption of HVP process)
- . Fast speed.
- . High breakdown voltage.
- . Adoption of MBIT process.

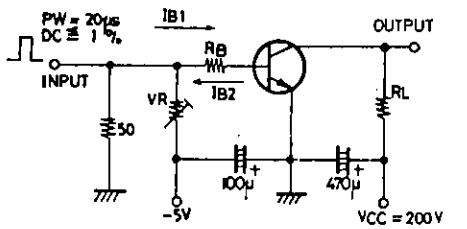
Absolute Maximum Ratings at Ta=25°C

Collector-to-Base Voltage	V _{CB0}		900	V
Collector-to-Emitter Voltage	V _{CE0}		500	V
Emitter-to-Base Voltage	V _{EB0}		7	V
Collector Current	I _C		15	A
Peak Collector Current	i _{cp}		25	A
Collector Dissipation	P _C	T _c =25°C	100	W
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

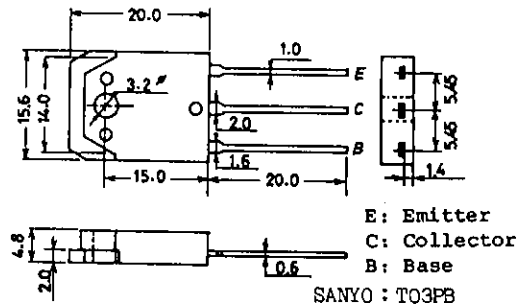
			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} =500V, I _E =0			10	μA
	I _{CES}	V _{CE} =900V, R _{BE} =0			0.5	mA
Collector-to-Emitter Sustain Voltage	V _{CEO(sus)}	I _C =100mA, I _B =0	500			V
Emitter Cutoff Current	I _{EB0}	V _{EB} =5V, I _C =0			1	mA
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =7V, I _B =1.4A			2	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =7A, I _B =1.4A			1.5	V
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =1.4A	8			
Storage Time	t _{stg}	I _C =7A, I _{B1} =1.4A, I _{B2} =-2.8A			3.0	μs
Fall Time	t _f	I _C =7A, I _{B1} =1.4A, I _{B2} =-2.8A		0.1	0.2	μs

Switching Time Test Circuit



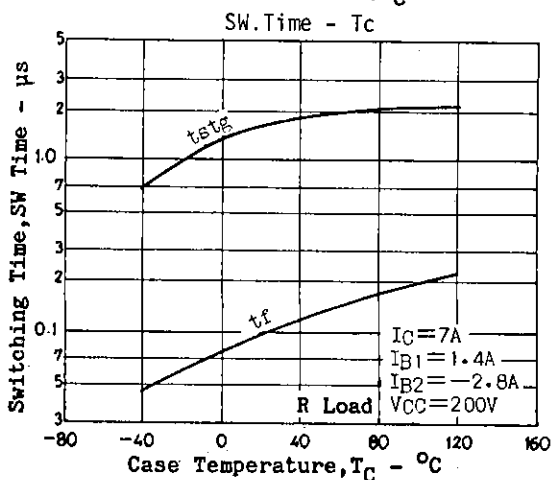
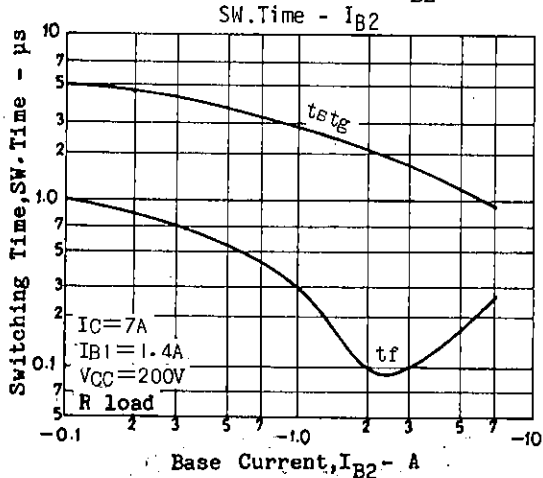
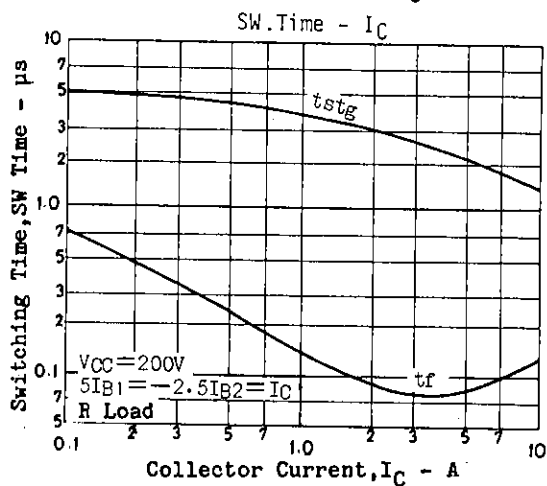
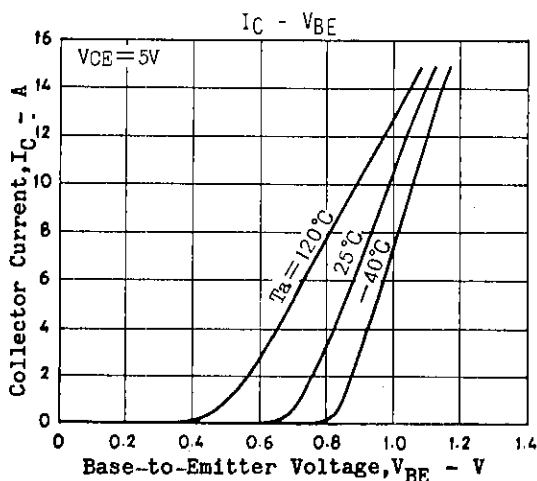
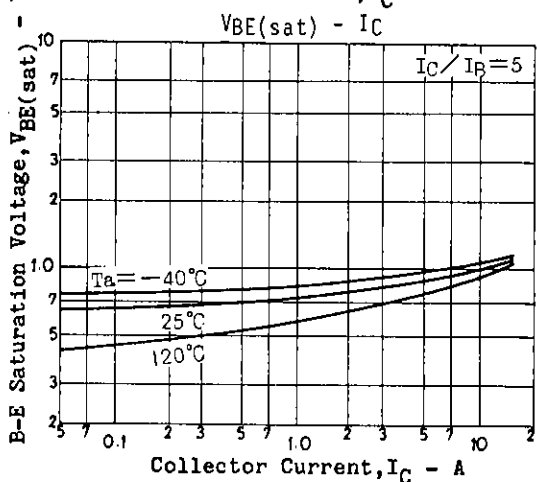
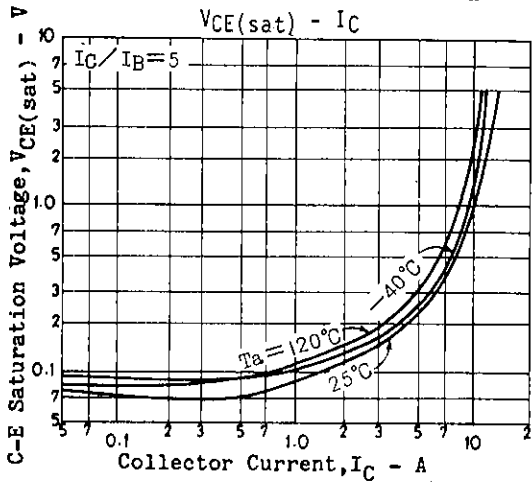
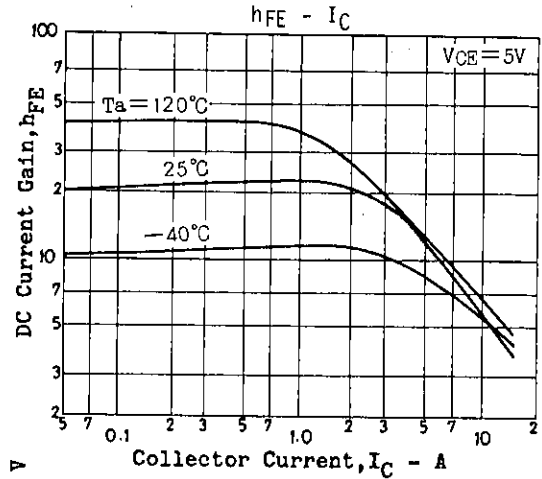
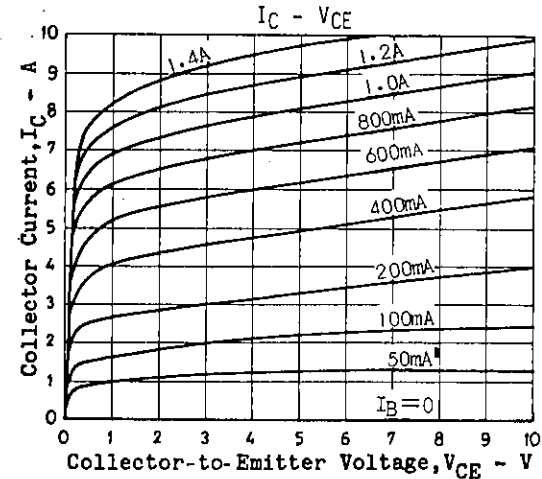
Unit (resistance:Ω, capacitance:F)

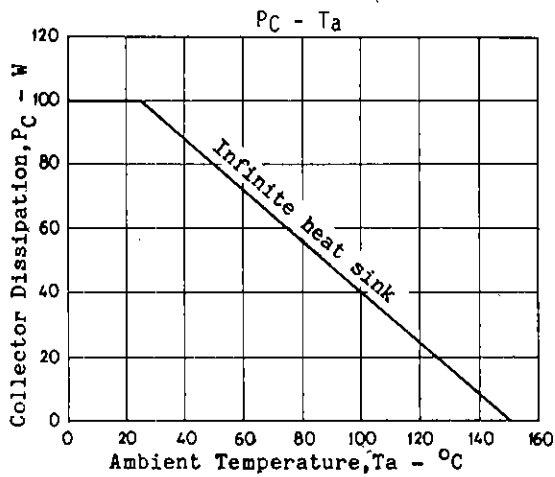
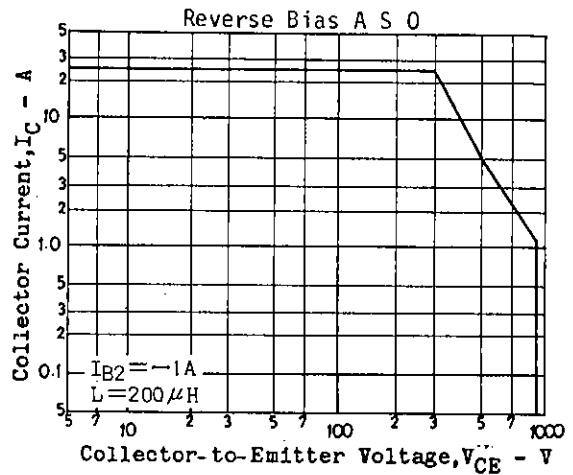
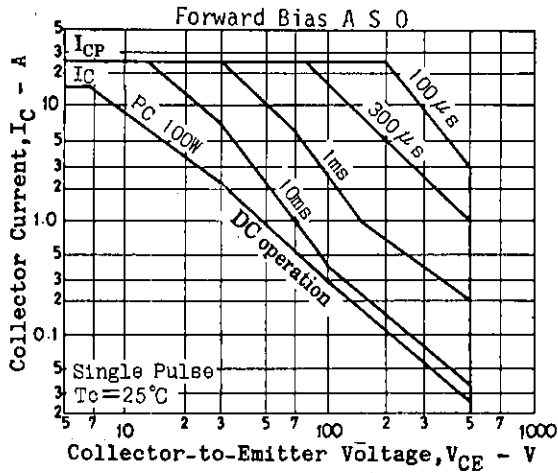
Package Dimensions 2022 (unit: mm)



E: Emitter
C: Collector
B: Base

SANYO : TO3PB





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